## Product Change Notice

**IRHMS67160 (2N7580T1)**

100V, N-Channel TID Hardened MOSFET in a Low Ohmic TO-254AA package.

### Radiation Characteristics Change:

Table 1 Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation

- **RDS(on) Static Drain-to-Source On-State Resistance (TO-3)**
  - For up to 300K Rads(Si), change from 0.010 ohm to 0.011 ohm maximum

Reference Datasheet PD-94723